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SPC-F005.DWG

REVISIONS

DOC. NO. SPC-F005 * Effective: 7/8/02 * DCP No: 1398

DCP #	REV	DESCRIPTION	DRAWN	DATE	CHECKD	DATE	APPRVD	DATE
2048	A	RELEASED	JN	05/21/09	JWM	05/21/09	JWM	05/21/09

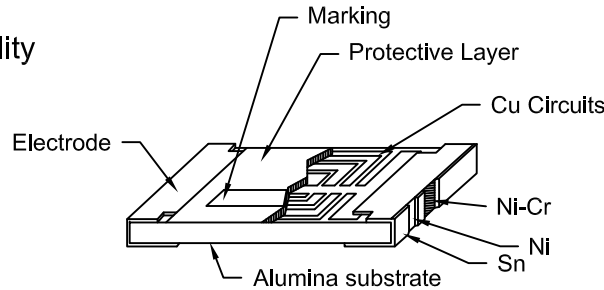
Features

- Photolithographic single layer ceramic chip
- High SRF, excellent Q, superior temperature stability
- Tight tolerance of $\pm 1\%$ or $\pm 0.1nH$
- Self resonant frequency controlled within 10%
- Stable inductance in high frequency circuit
- Highly stable design for critical needs

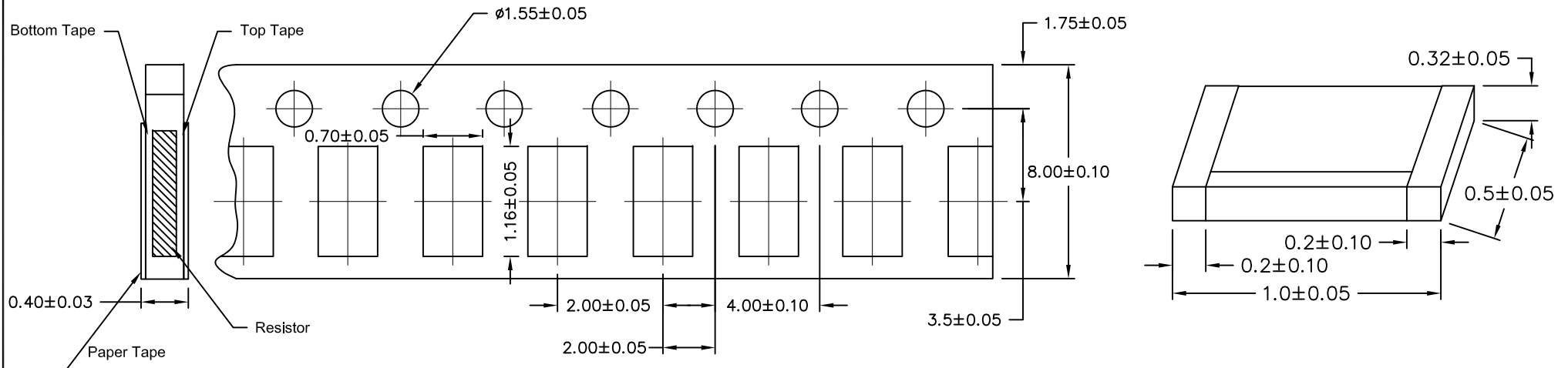


Application

- Cellular Phone, Pagers and GPS Products
- VCO, TCXO, Circuit an dRF Transceiver Module
- Wireless LAN Bluetooth module, Communication Appliances



Tape Dimension



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TOLERANCES:
UNLESS OTHERWISE SPECIFIED, DIMENSIONS ARE FOR REFERENCE PURPOSES ONLY.

DRAWN BY:	DATE:
Jason Nash	05/21/09
CHECKED BY:	DATE:
JWM	05/21/09
APPROVED BY:	DATE:
JWM	05/21/09

DRAWING TITLE: Thin Film Chip Inductor – Case size 0402			
SIZE	DWG. NO.	ELECTRONIC FILE	REV
A	Ta-1127	Ta-1127.DWG	A
SCALE: NTS	U.O.M.: Millimeters	SHEET: 1 OF 2	

Item		Specification	Test Method
1	Bending Test	As SPEC.	JIS-C-5202-6.1.4 Bending Amplitude 3mm for 10 seconds
2	Dielectric Withstand Voltage	>100V	MIL-STD-202F Method 301. Apply 100VA (rms) for 1minute.
3	Insulation Resistance	>1000MΩ	MIL-STD-202F Method 302 Apply 100VDC for 1minute.
4	Resistance to Soldering Heat	ΔL<10%	MIL-STD-202F Method 210E 260±5°C, 10±1seconds
5	High Temperature Exposure	ΔL<10%	JIS-C-5202-7.2 85±2°C, 1000 +48/-0 hours
6	Moisture Resistance	ΔL<10%	MIL-STD-202F Method 103B 40±2°C, 90~95%RH, 1000 +48/-0 hours
7	Low Temperature Storage	ΔL<10%	JIS-C-5202-7.1 -40±3°C, 1000 +48/-0 hours
8	Temperature Cycle	ΔL<10%	JIS-C-5202-7.4 -40/RT/85/RT, 10 cycles
9	Solderability	95% min coverage	MIL-STD-202F Method 208H 245°C ±5°C, 3±0.5(sec)

Mfr PN	Inductance	Inductance Tolerance	DC Resistance Max	DC Current Rating	Self Resonant Frequency	Package/ Case	Q Factor	Test Frequency
MCFT000000	1nH	±0.1 nH	0.15ohm	700mA	13GHz	402	Q Factor:13	500MHz
MCFT000001	1.5nH	±0.1 nH	0.25ohm	700mA	10GHz	402	Q Factor:13	500MHz
MCFT000002	2.2nH	±0.1 nH	0.35ohm	440mA	8GHz	402	Q Factor:13	500MHz
MCFT000003	3.3nH	±0.1 nH	0.45ohm	380mA	6GHz	402	Q Factor:13	500MHz
MCFT000004	4.7nH	±0.1 nH	0.65ohm	320mA	5GHz	402	Q Factor:13	500MHz
MCFT000005	6.8nH	±0.1 nH	1.05ohm	260mA	5GHz	402	Q Factor:13	500MHz
MCFT000006	8.2nH	±0.1 nH	1.25ohm	220mA	4GHz	402	Q Factor:13	500MHz
MCFT000007	10nH	±1%	1.35ohm	200mA	4GHz	402	Q Factor:13	500MHz
MCFT000008	15nH	±1%	1.75ohm	130mA	3GHz	402	Q Factor:13	500MHz
MCFT000009	22nH	±1%	2.65ohm	90mA	2GHz	402	Q Factor:13	500MHz
MCFT000010	33nH	±1%	4.5ohm	75mA	1.5GHz	402	Q Factor:13	500MHz